

10/540263

JC17 Rec'd PCT/PTO 23 JUN 2005

00862;102566.

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
KIYOFUMI SAKAGUCHI, ET AL.) Examiner: Not Yet Assigned
Application No.: Not Yet Assigned) Group Art Unit: Not Yet Assigned
Filed: Herewith)
For: SEMICONDUCTOR SUBSTRATE,)
MANUFACTURING METHOD)
THEREOF, AND)
SEMICONDUCTOR DEVICE : June 22, 2005

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the non-U.S. documents listed on the enclosed Form PTO-1449. Copies of the listed documents are also enclosed.

For a concise explanation of relevance of the non-English documents, the Examiner is referred to the enclosed English-language abstracts, and to pages 2 and 13 of the specification.

Some of the listed documents were cited in a PCT International Search Report mailed February 8, 2005 for International Application No. PCT/JP2004/018982, which is the parent of the present application from which this application claims priority. A copy of this search report is also enclosed.

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Some of the listed documents were cited in a PCT International Search Report mailed March 29, 2005 for International Application No. PCT/JP2004/018981, which is the parent of the present application from which this application claims priority. A copy of this search report is also enclosed.

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our address given below.

Respectfully submitted,


John A. Krause
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ATTY DOCKET NO.

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APPLICANT

KIYOFUMI SAKAGUCHI, ET AL. KUMONI

FILING DATE

HEREWITH

GROUP

NOT YET ASSIGNED

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,221,413	06/22/93	Brasen, et al.	117	89	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
	JPA	2003-78118	03/14/03	Japan			Abstract
	JPA	2003-78140	03/14/03	Japan			Abstract
	JPA	2003-178977	06/27/03	Japan			Abstract
	JPA	2003-282464	10/03/03	Japan			Abstract
	JPA	2003-282463	10/03/03	Japan			Abstract
	JPA	2004-342975	12/02/04	Japan			Abstract
	JPA	11-195562	07/21/99	Japan			Abstract
	JPA	07-302889	11/14/95	Japan			Abstract
	EP	1248294 A2	10/09/02	EPO			

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

		Current, I, Michael., et al. "Atomic-Layer Cleaving with Si _x Ge _y Strain Layers For Fabrication of Si and Ge-rich SOI Device Layers" IEEE International SOI Conference, October 1, 2001, pp. 11-12.
		Shin-ichi Takagi, "Metal-Oxide-Semiconductor (MOS) device technologies using Si/Ge heretointerfaces", Oyo Buturi, Vol. 72, NO. 3, pp. 284-290, 2003.
		T.A. Langdo, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 4256-4258 (2003).
		D.J. Godbey, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 373-379 (1990).
		D. Ferijoo, et al., J. Electro. Mat., vol. 23, no. 6, pp. 493-496 (1994).
		A.H. Krist, et al., Appl. Phys. Lett., vol. 58, no. 17, pp. 1899-1901 (1991).

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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